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IGINEERING				
Duration: 3 Hours				
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Reg No.:_____ Name:____

APJ ABDUL KALAM TECHNOLOGICAL UNIVERSIT

FIRST SEMESTER B.TECH DEGREE EXAMINATION, DECEMBER

		Course Code: EC100			
Course Name: BASICS OF ELECTRONICS ENGINEERING					
Ma	x. M	arks: 100 Duration: 3	Hours		
PART A					
		Answer all questions, each carries 5 marks.	Marks		
1		With the help of neat diagram, explain the construction and working of electrolytic capacitor.	(5)		
2		With the help of energy band diagram explain insulators, conductors and semiconductors.	(5)		
3		Draw the block diagram of a DC power supply and mention the functions of each block.	(5)		
4		Why are universal gates called so? Realize a two input OR gate using any one of the universal gates.	(5)		
5		Write main features of the orbit of a geo stationary satellite.	(5)		
6		Draw the frequency spectrum of an amplitude modulated (AM) wave. Given that	(5)		
		modulating signal is of frequency fm, amplitude V_m and carrier of frequency fc, amplitude V_c . Take modulation index as m. What is the bandwidth requirement of this AM wave?			
7		Draw and explain the structure of an optical fiber cable.	(5)		
8		With supporting diagram explain frequency reuse done in cellular communication.	(5)		
		PART B			
Answer six questions, one full question from each module and carries 10 marks.					
		Module I			
9	a)	Write the significance of specifying tolerance value of a component. A ceramic capacitor has got the following code marked on its surface. Identify the capacitance value. (i) 103J (ii) 2n2	(5)		
	b)	Explain the basic working principle of transformer. Write the equation relating primary and secondary voltages to turns ratio.	(5)		
		OR			
10	a)	Explain the working of electromagnetic relays.	(5)		
	b)	Write and explain any five applications of Electronics in industry.	(5)		
		Module II			
11		With neat diagrams, explain the input and output characteristics of a common emitter NPN transistor.	(10)		
	OR				
12	a)	Derive the relation between α and β for a transistor. For an npn transistor, α =	(5)		

0.995 and $I_E = 10$ mA. Find I_B and I_C . b) Explain the diode equation. The forward current flowing through a diode at room (5)temperature is 1mA when the forward bias applied is 0.2V. The reverse saturation current through the diode is 0.45µA at room temperature. Determine whether the diode is made up of Silicon or Germanium. **Module III** 13 a) Draw the block diagram of a public-address system and specify the functions of (5) b) Draw the circuit diagram of an RC phase shift oscillator and explain the need of (5)each component. OR 14 With suitable circuit diagram explain how a Zener diode can be used as a voltage (10) regulator. Differentiate between line regulation and load regulation. **Module IV** Draw the functional block diagram of an operational amplifier. Define any two 15 a) (5) parameters and specify its ideal values. b) Draw circuit diagram and derive expressions for gain of inverting and non-(5) inverting amplifier using Op-Amp. OR 16 a) Explain the working of digital multimeter with a block diagram. (5) b) Draw the block diagram of Digital Storage Oscilloscope and explain the working (5) Module V 17 a) Explain satellite communication system with block diagram. (5)b) Explain advantages and disadvantages of satellite communication. Specify one (5)frequency band used for satellite communication. Draw block diagram and explain functioning of superheterodyne receiver. (5) Write the principle of frequency modulation and list the advantages of FM over (5)AM. Module VI 19 What is meant by critical angle? What is its significance in optical fiber a) (5) communication? b) Draw and explain functional block diagram of cellular communication system (5) 20 a) Use block diagram representation to explain the functioning of DTH. (5)With the help of suitable diagrams, explain the working of CCTV. Give one (5) application. *****